

Silicon NPN Power Transistor

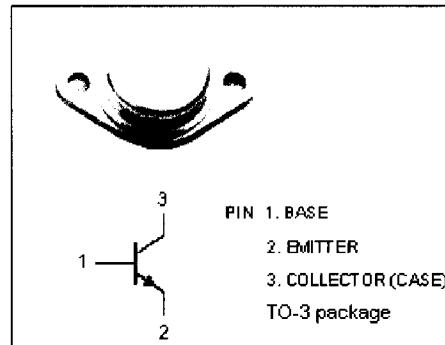
BUY71

DESCRIPTION

- High Switching Speed
- Collector-Emitter Sustaining Voltage-
 : $V_{CEQ(SUS)} = 800V$ (Min)

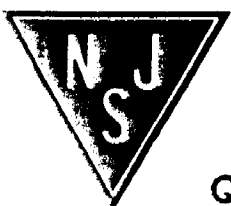
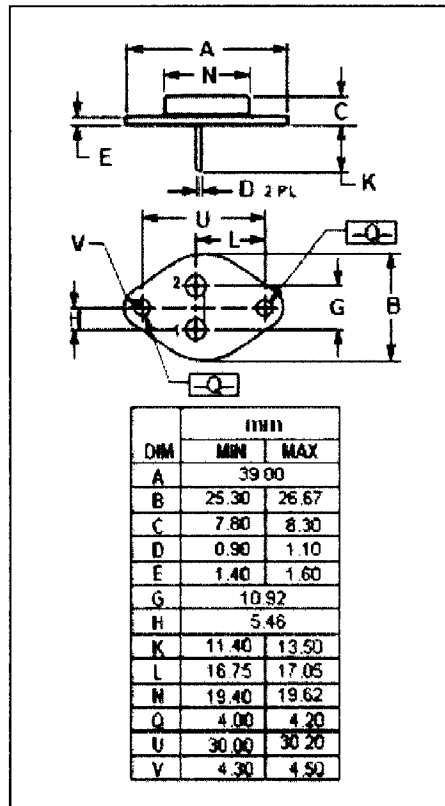
APPLICATIONS

- Designed for use in high voltage CRT scanning applications.



ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	1600	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	2	A
I_B	Base Current	2	A
P_C	Collector Power Dissipation @ $T_c = 25^\circ C$	40	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



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Silicon NPN Power Transistor**BUY71****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-Emitter Sustaining Voltage	I _C = 10mA; I _B = 0	800			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 0.1A; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 1.5A; I _B = 1.5A			10	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 1.5A; I _B = 1.5A			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} =1600; I _E = 0			1.0	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			1.0	mA
h _{FE}	DC Current Gain	I _C = 0.5A; V _{CE} = 5V	8			
t _f	Fall Time	I _C = 1.2A			0.7	μs